

NPN/PNP high power double bipolar transistor 14 October 2014 P

Product data sheet

1. General description

NPN/PNP high power double bipolar transistor in a SOT1205 (LFPAK56D) Surface-Mounted Device (SMD) power plastic package.

NPN/NPN complement: PHPT610030NK.

PNP/PNP complement: PHPT610030PK.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Motor control
- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Relay replacement

4. Quick reference data

Table 1. Qui	ck reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Per transistor	Per transistor; for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	100	V	
I _C	collector current			-	-	3	А	
TR1 (NPN)								
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 3 A; I_{B} = 300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	75	110	mΩ	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR2 (PNP)						
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	110	180	mΩ

5. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	E1	emitter TR1	8 7 6 5	C1 B2 E2	
2	B1	base TR1			
3	E2	emitter TR2			
4	B2	base TR2			
5	C2	collector TR2			
6	C2	collector TR2			sym139
7	C1	collector TR1	1 2 3 4 LFPAK56D (SOT1205)		
8	C1	collector TR1	(0011200)		

6. Ordering information

Table 3. Ordering information						
Type number	Package	kage				
	Name	Description	Version			
PHPT610030NPK	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

1	Table 4. Marking codes	
•	Type number	Marking code
	PHPT610030NPK	1003NPK

NPN/PNP high power double bipolar transistor

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Per transis	tor; for the PNP transistor with	negative polarity				
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1	W
		T _{amb} ≤ 25 °C	[2]	-	2.4	W
			[3]	-	25	W
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[4]	-	5	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

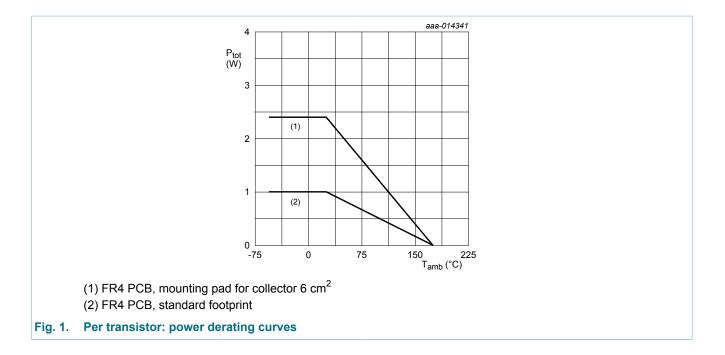
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Power dissipation from junction to mounting base.

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

NPN/PNP high power double bipolar transistor



9. Thermal characteristics

Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor	I			_		
frc	thermal resistance	in free air	[1]	-	-	150	K/W
	from junction to ambient	!	[2]	-	-	62.5	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W
Per device							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	120	K/W
	from junction to ambient		[2]	-	-	50	K/W
	ampient		[3]	-	-	30	K/W

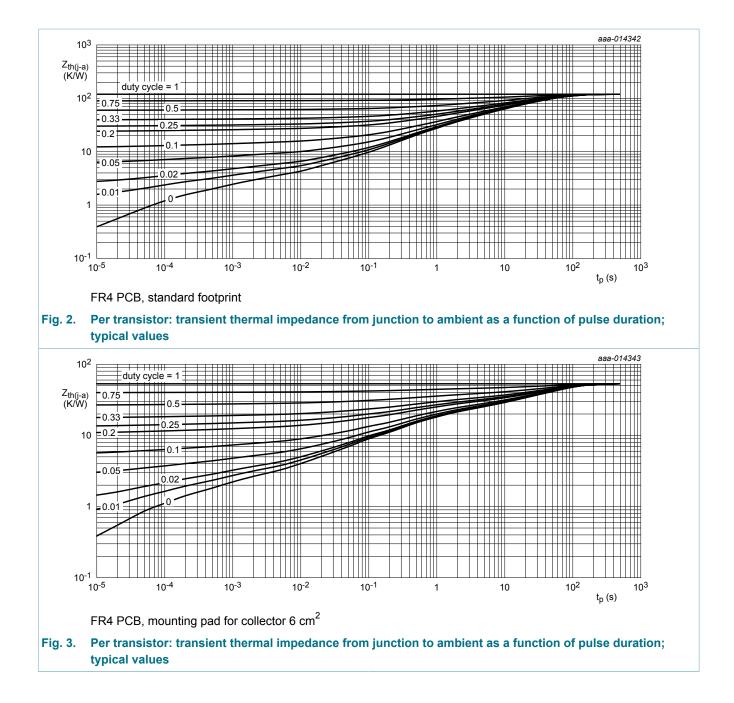
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

PHPT610030NPK

NPN/PNP high power double bipolar transistor



NPN/PNP high power double bipolar transistor

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1 (NPN)			I			
I _{CBO} collector-base cut-off		V_{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	$\begin{split} V_{CE} &= 10 \text{ V}; \text{ I}_{C} = 500 \text{ mA}; \text{pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	150	250	-	
		V_{CE} = 10 V; I _C = 1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	80	250	-	
		$V_{CE} = 10 \text{ V}; \text{ I}_{C} = 2 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C}$	20	100	-	
		$\begin{split} V_{CE} &= 10 \text{ V}; \text{ I}_{C} = 3 \text{ A}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta &\leq 0.02; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	10	40	-	
ologi	collector-emitter saturation voltage	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	90	150	mV
		$\begin{split} I_{C} = 3 \text{ A}; \ I_{B} = 0.3 \text{ A}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02; \ T_{\text{amb}} = 25 \ ^{\circ}\text{C} \end{split}$	-	225	330	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	75	110	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	0.86	1	V
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	1	1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.67	0.85	V
t _d	delay time	V_{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	140	-	MHz

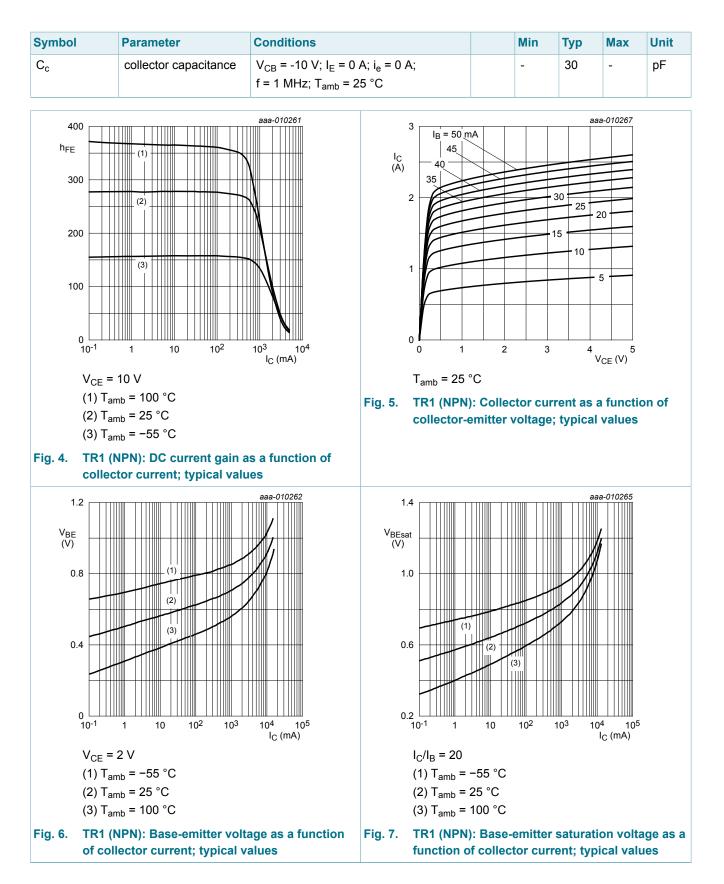
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}; \text{ i}_{\text{e}} = 0 \text{ A};$ f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF
TR2 (PNP)	L					
I _{CBO}	collector-base cut-off	V _{CB} = -80 V; I _E = 0 A	-	-	-100	nA
	current	V_{CB} = -80 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -80 V; V _{BE} = 0 V	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -7 V; I _C = 0 A	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C	150	200	-	
		V_{CE} = -10 V; I _C = -1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	80	210	-	
		V_{CE} = -10 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	20	100	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -3 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C}$	10	40	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-70	-110	mV
		I_{C} = -2 A; I_{B} = -0.2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-220	-360	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	110	180	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.91	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$\begin{split} V_{CE} &= -2 \text{ V; } \text{I}_{C} = -100 \text{ mA; pulsed;} \\ t_{p} &\leq 300 \mu\text{s; } \delta \leq 0.02\text{; } \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-0.68	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I_{C} = -1 A; I_{Bon} = -50 mA;	-	20	-	ns
t _r	rise time	I_{Boff} = 50 mA; T_{amb} = 25 °C	-	180	-	ns
t _{on}	turn-on time		-	200	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	570	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	125	-	MHz

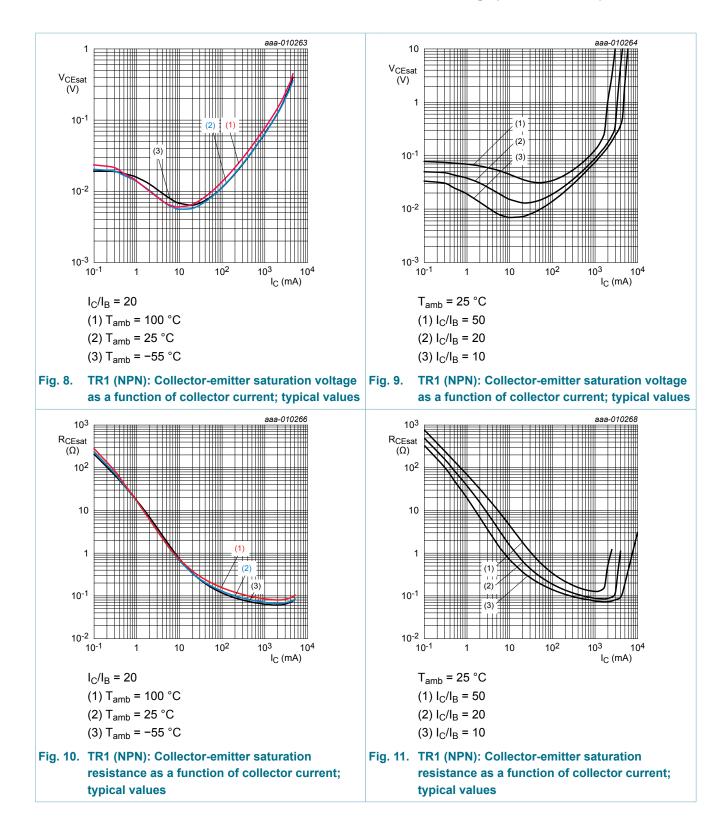
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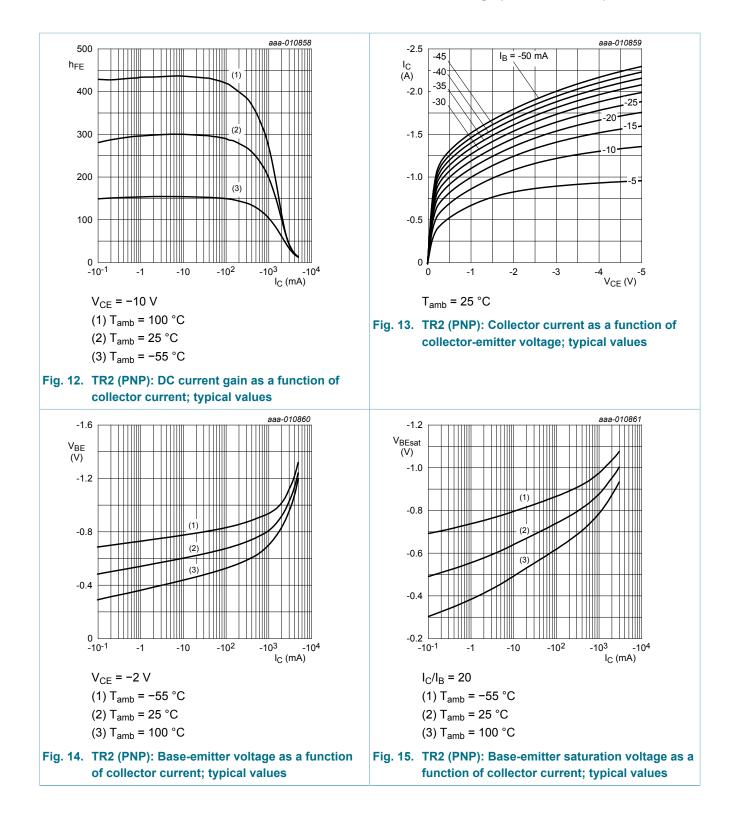


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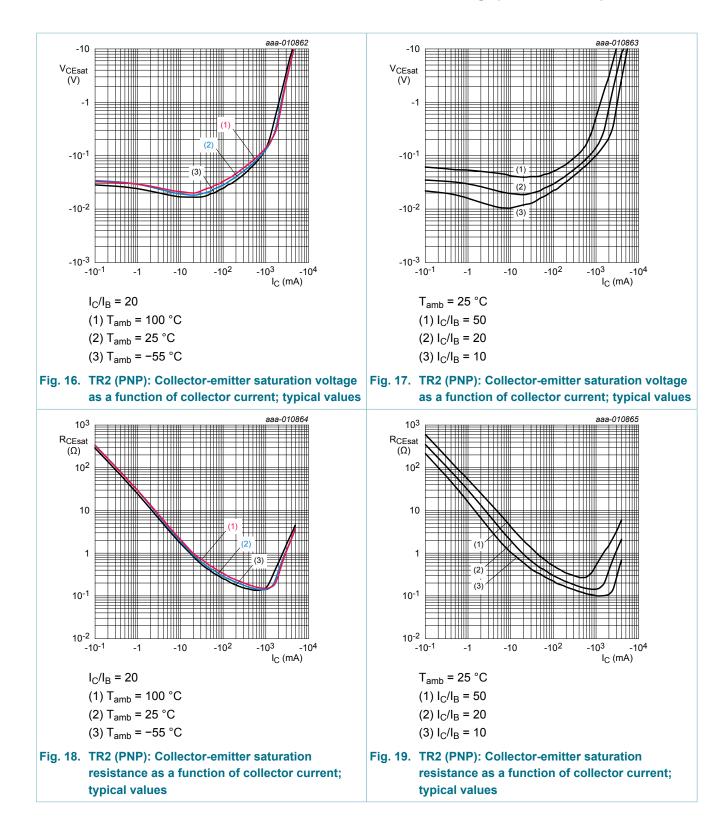
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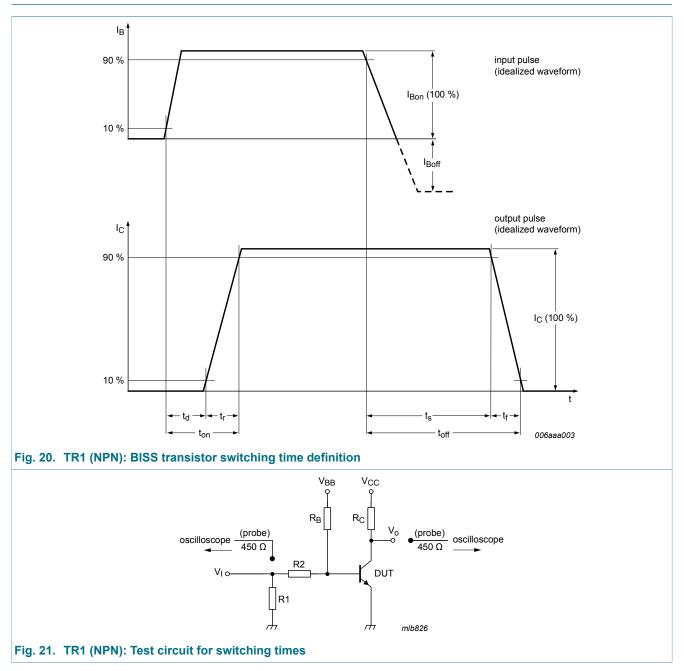
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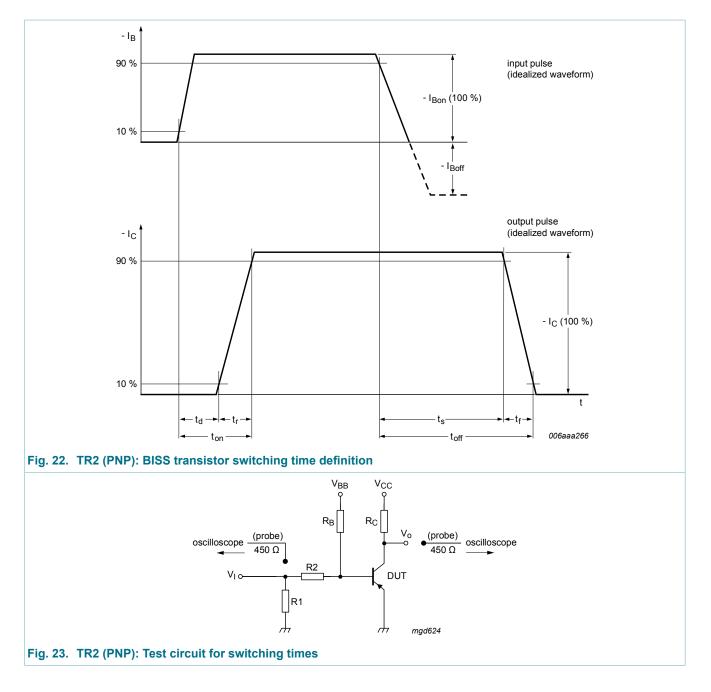
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11. Test information

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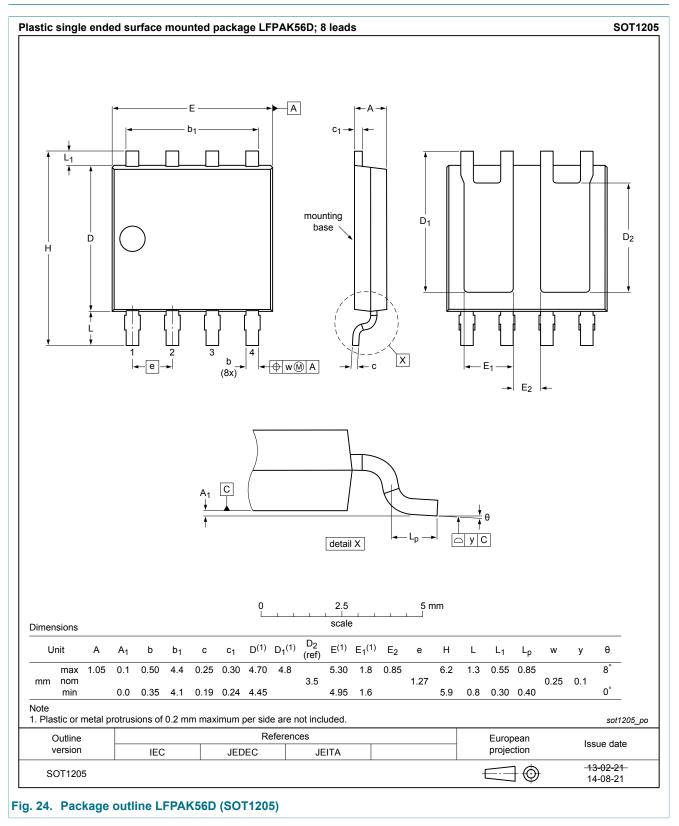


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

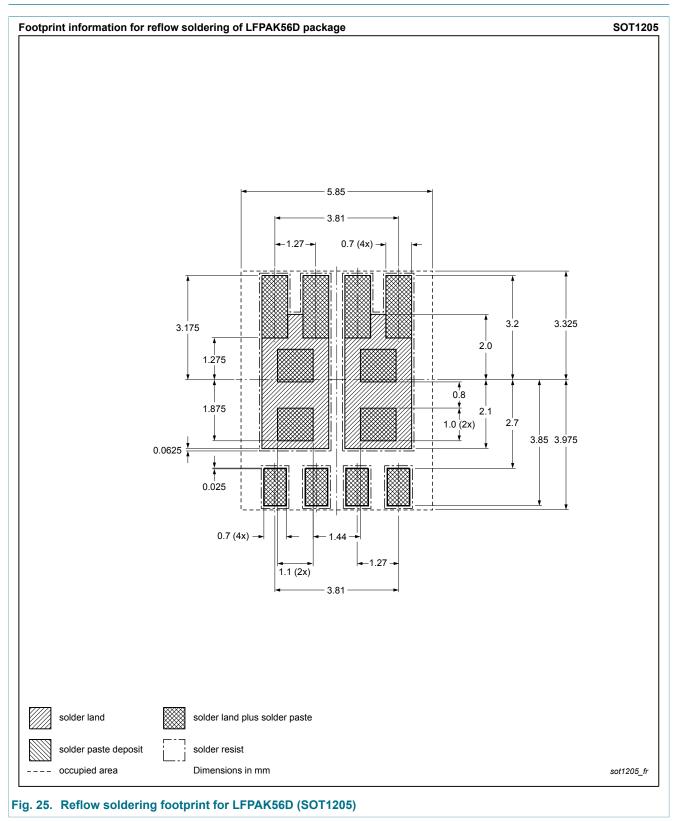


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13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PHPT610030NPK v.1	20141014	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NPN/PNP high power double bipolar transistor

16. Contents

1	General description1
2	Features and benefits1
3	Applications1
4	Quick reference data1
5	Pinning information2
6	Ordering information2
7	Marking2
8	Limiting values3
9	Thermal characteristics4
10	Characteristics6
11	Test information12
11.1	Quality information 13
12	Package outline14
13	Soldering15
14	Revision history16
15	Legal information17
15.1	Data sheet status 17
15.2	Definitions17
15.3	Disclaimers17
15.4	Trademarks

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